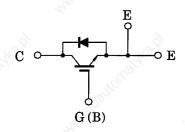
TOSHIBA GTR Module Silicon N Channel IGBT

MG200Q1US51

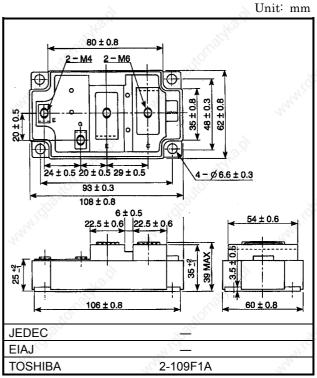
High Power Switching Applications Motor Control Applications

- High input impedance
- High speed: tf = 0.3µs (Max.) @Inductive load
- Low saturation voltage
 - $: V_{CE (sat)} = 3.6V (Max.)$
- Enhancement-mode
- The electrodes are isolated from case.

Equivalent Circuit



Maximum Ratings (Ta = 25°C)



Weight: 465g

Characteristic Collector-emitter voltage Gate-emitter voltage		Symbol	Rating	Unit V V	
		V _{CES}	1200		
		V _{GES}	±20		
Collector current	DC	I _C (25°C / 80°C)	300 / 200	A	
	1ms	I _{CP} (25°C / 80°C)	600 / 400	^	
Forward Current	DC	IE COLO	200	A	
	1ms	I _{FM}	400		
Collector power dissipation (Tc = 25°C)		P _C	1500	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	٧	
Screw torque (Terminal: M4/M6/mounting)		*O(L)	2/3/3	N·m	

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damage to property.

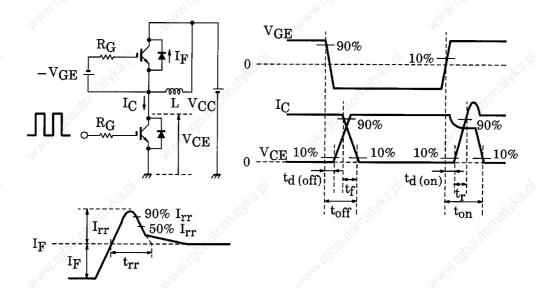
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TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general
can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the
buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and
to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or
damage to property.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0		They	_	±500	nA
Collector cut-off current		I _{CES}	V _{CE} = 1200V, V _{GE} = 0		_	_	4.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 200mA, V _{CE} = 5V		3.0	_	6.0	٧
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 200A V _{GE} = 15V	T _j = 25°C	_	2.8	3.6	V
				T _j = 125°C	_	3.1	4.0	
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz		89	24.0	_	nF
Switching time	Turn-on delay time	t _{d (on)}	Inductive load $\begin{array}{c} \text{V}_{CC} = 600\text{V} \\ \text{I}_{C} = 200\text{A} \\ \text{V}_{GE} = \pm 15\text{V} \\ \text{R}_{G} = 4.7\Omega \end{array}$ (Note 1)		44.	0.05	_	μs
	Rise time	t _r			7.	0.05	_	
	Turn-on time	t _{on}			_	0.2	9	
	Turn-off delay time	t _d (off)			_	0.5	<u> </u>	
	Fall time	to			_	0.1	0.3	
	Turn-off time	t _{off}			00	0.6	_	
Forward voltage		V _F	I _F = 200A, V _{GE} = 0		" HAT	2.4	3.5	V
Reverse recovery time		t _{rr}	I _F = 200A, V _{GE} = -10V di / dt = 700A / μs (Note 1)			0.15	0.3	μs
Thermal resistance		R _{th (j-c)}	Transistor stage		_	_	0.08	°C /\\
			Diode stage	(A)	_	- A	0.24	°C/W

Note 1: Switching time and reverse recovery time test circuit & timing chart

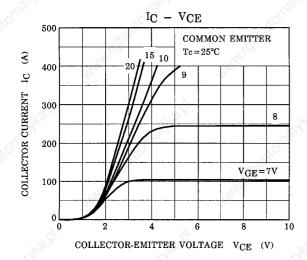


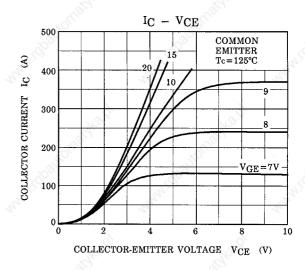
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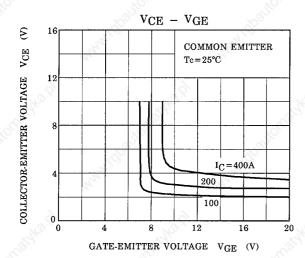
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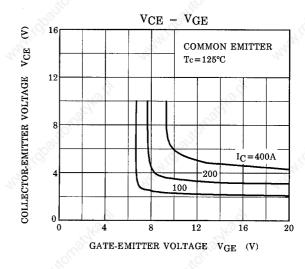
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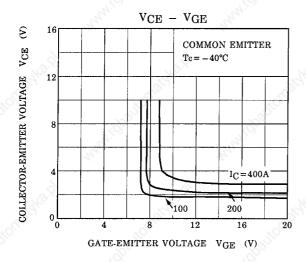
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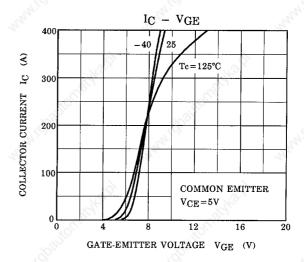


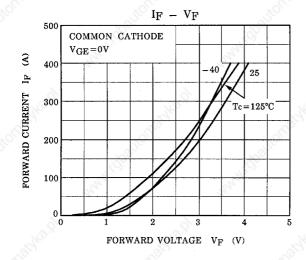


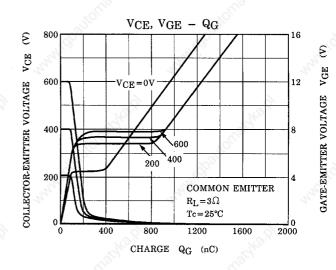


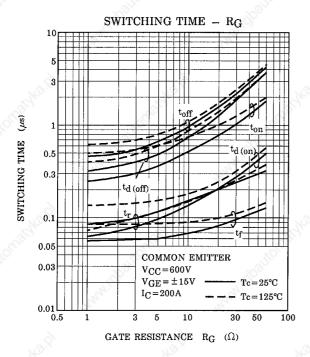


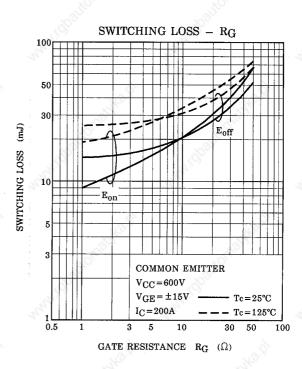


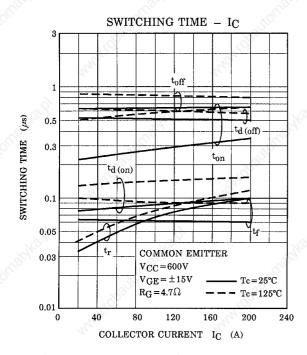


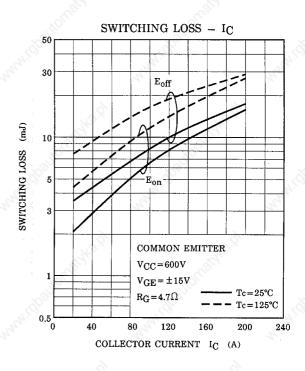


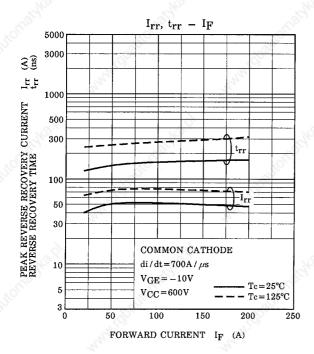


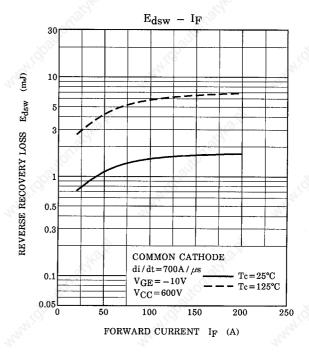


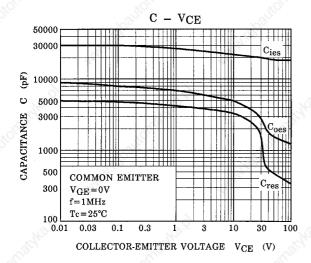


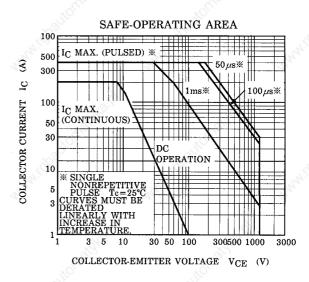


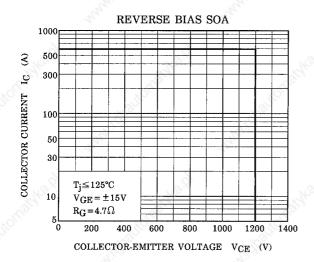


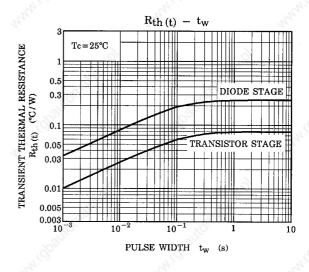


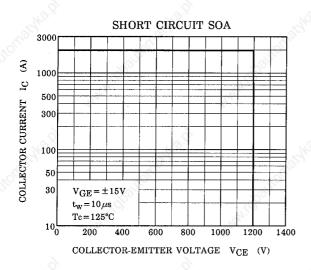












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